

CBCS SCHEME

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18EE34

Third Semester B.E. Degree Examination, Feb./Mar. 2022

Analog Electronic Circuits

Time: 3 hrs.

Max. Marks: 100

Note: Answer any FIVE full questions, choosing ONE full question from each module.

Module-1

- 1 a. For the circuit shown in Fig Q1(a) sketch the output waveforms and transfer characteristics for cut in voltage of diode is 0.7V

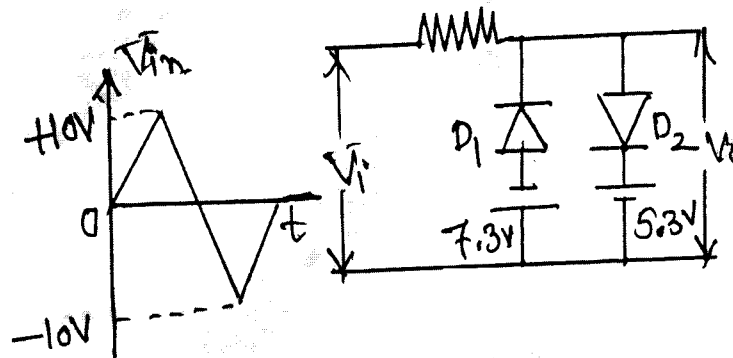


Fig Q1(a)

(08 Marks)

- b. With a neat circuit diagram, explain self bias circuit, write the necessary equations. (08 Marks)
- c. Define stability factor and derive the expression for stability factor of fixed base circuit with respect to I_{CO} . (04 Marks)

OR

- 2 a. Derive an expression for E_{Th} , I_B and V_{CE} for voltage divider bias circuit using exact analysis. (08 Marks)
- b. What is clamping circuit? Explain the negative clamping circuit with and without reference voltage with necessary waveforms. (08 Marks)
- c. List the important applications of clipping and clamping circuits. (04 Marks)

Module-2

- 3 a. With the help of r_e equivalent model, derive an equation for Z_i , Z_o and A_V for an emitter follower configuration. (08 Marks)
- b. State and prove Millers theorem. (08 Marks)
- c. Compare the characteristics of CB, CC and CE configurations. (04 Marks)

OR

- 4 a. Starting from fundamental define h-parameters and obtain an h-parameter equivalent circuit of common emitter configuration. (08 Marks)

Important Note : 1. On completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages.
2. Any revealing of identification, appeal to evaluator and/or equations written eg, 42+8 = 50, will be treated as malpractice.

- b. For the circuit shown below, determine : i) r_e ii) Z_i , Z_o , A_v and A_i taking $r_o = \infty \Omega$

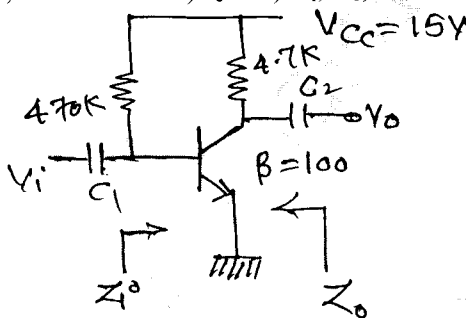


Fig Q4(b)

(08 Marks)

- c. What are the advantages of h-parameters?

(04 Marks)

Module-3

- 5 a. Derive expressions for Z_i , Z_o and A_i for a Darlington emitter follower circuit. (10 Marks)
 b. Draw and explain the block diagram of multistage cascade amplifier. (06 Marks)
 c. Write important characteristics of Darlington emitter follower. (04 Marks)

OR

- 6 a. For a current series feedback amplifier, derive an expression for Z_{if} and Z_{of} . (10 Marks)
 b. Explain the general characteristics of negative feedback amplifier. (10 Marks)

Module-4

- 7 a. Explain the operation of class B push-pull amplifier. Prove that the maximum efficiency of class B configuration is 78.5%. (08 Marks)
 b. With a neat diagram and waveform, explain the operation of RC phase shift oscillator using BJT. Write the expression for frequency of oscillation. (08 Marks)
 c. A crystal has following parameters $L = 0.3344\text{H}$, $C = 0.065\text{pF}$, $C_M = 1\text{pF}$ and $R = 5.5\text{K}\Omega$. Calculate : i) Series resonance frequency ii) Parallel resonance frequency. (04 Marks)

OR

- 8 a. With a neat diagram, explain basic principle of operation of oscillators and write the condition to obtain sustained oscillations. (08 Marks)
 b. Prove that the maximum conversion efficiency of class A transformer coupled amplifier is 50%. (08 Marks)
 c. The following readings are available for a power amplifier, calculate the second harmonic distortion in each case.

$$V_{CEQ} = 10\text{V} \quad V_{CE(\max)} = 18\text{V} \quad V_{CE(\min)} = 1\text{V}$$

$$V_{CEQ} = 10\text{V} \quad V_{CE(\max)} = 19\text{V} \quad V_{CE(\min)} = 1\text{V}$$

(04 Marks)

Module-5

- 9 a. Explain the construction working and characteristics of an n-channel JFET. (10 Marks)
 b. Define transconductance (g_m) and derive an expression for " g_m ". (06 Marks)
 c. Compare BJT and JFET. (04 Marks)

OR

- 10 a. With neat sketch, explain the basic construction operation and characteristic of n-channel depletion type MOSFET. (10 Marks)
 b. Derive the expression for A_v , Z_i and Z_o for a JFET common source amplifier with fixed bias configuration. (10 Marks)

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